

SN74ACT139-Q1 Automotive Dual 2- to 4-Bit Decoders/Demultiplexers with TTL-Compatible Inputs

1 Features

- AEC-Q100 qualified for automotive applications:
 - Device temperature grade 1: -40°C to +125°C
 - Device HBM ESD classification level 2
 - Device CDM ESD classification level C4B
- Available in [wetable flank](#) QFN package
- Operating voltage range of 4.5V to 5.5V
- TTL-compatible inputs
- Continuous ±24mA output drive at 5V
- Supports up to ±75mA output drive at 5V in short bursts
- Drives 50Ω transmission lines
- Fast operation with delay of 10.2ns max

2 Applications

- Memory device selection with shared data bus
- Reduce required number of outputs for chip select applications
- Route data

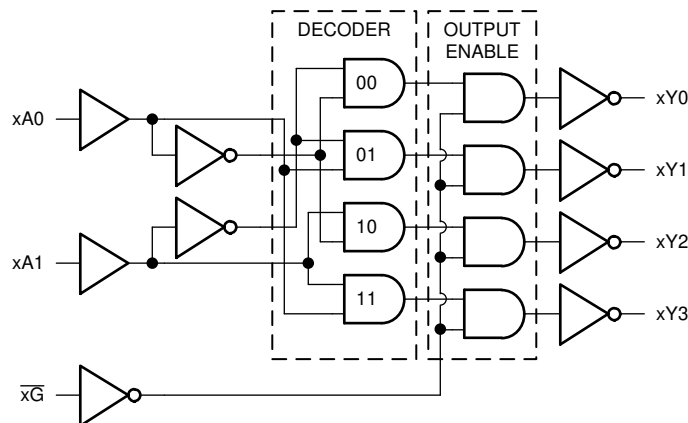
3 Description

The SN74ACT139-Q1 contains two two-to-four decoders with one active low output strobe (\overline{G}). When the strobe input is inactive ($\overline{G} = \text{HIGH}$), the outputs for that channel are all forced into the high state. When strobe input is active ($\overline{G} = \text{LOW}$), only the selected output is low while all others are high.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE ⁽³⁾
SN74ACT139-Q1	BQB (WQFN, 16)	3.5mm × 2.5mm	3.5mm × 2.5mm
	PW (TSSOP, 16)	5mm × 6.4mm	5mm × 4.4mm

- (1) For more information, see [Section 11](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.



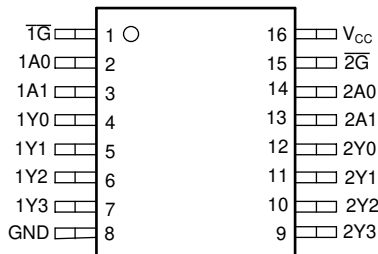
Functional Diagram



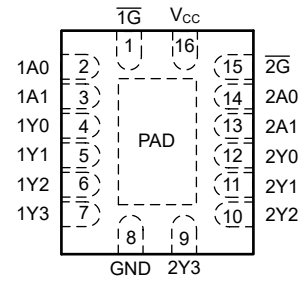
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4 Pin Configuration and Functions



PW Package, 16-Pin TSSOP (Top View)



BQB Package, 16-Pin WQFN (Transparent Top View)

Table 4-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NO.	NAME		
1	$\overline{1G}$	I	Channel 1, output strobe, active low
2	1A ₀	I	Channel 1, address select 0
3	1A ₁	I	Channel 1, address select 1
4	1Y ₀	O	Channel 1, output 0
5	1Y ₁	O	Channel 1, output 1
6	1Y ₂	O	Channel 1, output 2
7	1Y ₃	O	Channel 1, output 3
8	GND	—	Ground
9	2Y ₃	O	Channel 2, output 3
10	2Y ₂	O	Channel 2, output 2
11	2Y ₁	O	Channel 2, output 1
12	2Y ₀	O	Channel 2, output 0
13	2A ₁	I	Channel 2, address select 1
14	2A ₀	I	Channel 2, address select 0
15	$\overline{2G}_0$	I	Channel 2, output strobe, active low
16	V _{CC}	—	Positive supply
Thermal Pad ⁽²⁾		—	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

(2) BQB package only.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	7	V
V _I	Input voltage range ⁽²⁾		-0.5	V _{CC} + 0.5V	V
V _O	Output voltage range ⁽²⁾		-0.5	V _{CC} + 0.5V	V
I _{IK}	Input clamp current	V _I < -0.5V or V _I > V _{CC} + 0.5V		±20	mA
I _{OK}	Output clamp current	V _O < -0.5V or V _O > V _{CC} + 0.5V		±50	mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±50	mA
	Continuous output current through V _{CC} or GND			±200	mA
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

- (1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		4.5	5.5	V
V _{IH}	High-level input voltage		2		V
V _{IL}	Low-Level input voltage			0.8	V
V _I	Input Voltage		0	V _{CC}	V
V _O	Output Voltage		0	V _{CC}	V
I _{OH}	High-level output current			-24	mA
I _{OL}	Low-level output current			24	mA
Δt/Δv	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		-40	125	°C

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC ⁽¹⁾						UNIT
		R _{θJA}	R _{θJC(top)}	R _{θJB}	Ψ _{JT}	Ψ _{JB}	R _{θJC(bot)}	
PW (TSSOP)	16	126.2	60.5	84.2	7.5	83.3	-	°C/W
BQB (WQFN)	16	91.2	95.1	61.4	18.0	61.2	38.0	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
V _{OH}	I _{OH} = -50µA	4.5V	4.4	4.499	V	
		5.5V	5.4	5.499		
	I _{OH} = -24mA	4.5V	3.7			
		5.5V	4.7			
V _{OL}	I _{OL} = 50µA	4.5V		0.001	0.1	
		5.5V		0.001	0.1	
	I _{OL} = 24mA	4.5V			0.5	
		5.5V			0.5	
I _I	V _I = 5.5V or GND	0V to 5.5V			±1	µA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5V			2	µA
ΔI _{CC}	V _I = V _{CC} - 2.1V; Any Input	4.5V to 5.5V			200	µA
C _I	V _I = V _{CC} or GND	5V		2		pF
C _{PD} (1) (2)	C _L = 50pF, F = 1MHz	5V		57		pF

- (1) C_{PD} is used to determine the dynamic power consumption, per channel
- (2) P_D = V_{CC}² × F_I × (C_{PD} + C_L) where F_I = input frequency, C_L = output load capacitance, V_{CC} = supply voltage
- (3) Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.

5.6 Switching Characteristics

C_L = 50 pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	-40°C to 125°C			UNIT
				MIN	TYP	MAX	
t _{phl}	Any A	Any Y	5V		6.9	10.2	ns
t _{plh}	Any A	Any Y	5V		6.3	9.5	ns
t _{phl}	\bar{G}	Any Y	5V		7.3	10.4	ns
t _{plh}	\bar{G}	Any Y	5V		6.3	9.3	ns

5.7 Typical Characteristics

T_A = 25°C (unless otherwise noted)

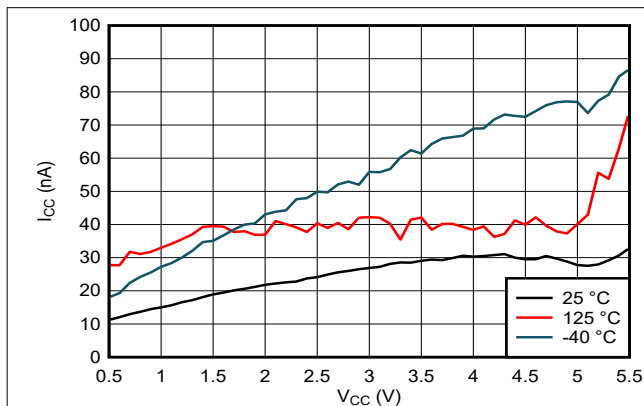


Figure 5-1. Supply Current Across Supply Voltage

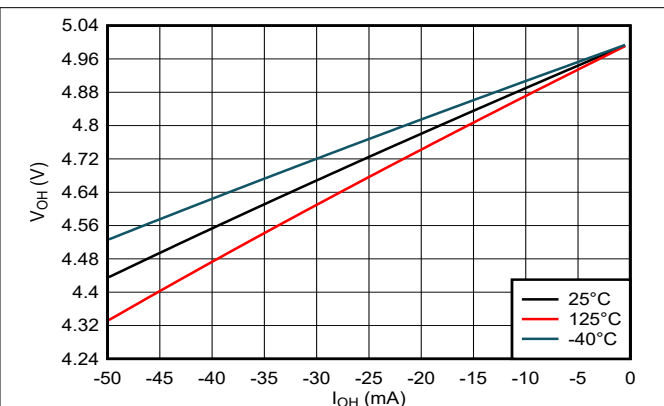


Figure 5-2. Output Voltage vs Current in HIGH State; 5V Supply

5.7 Typical Characteristics (continued)

T_A = 25°C (unless otherwise noted)

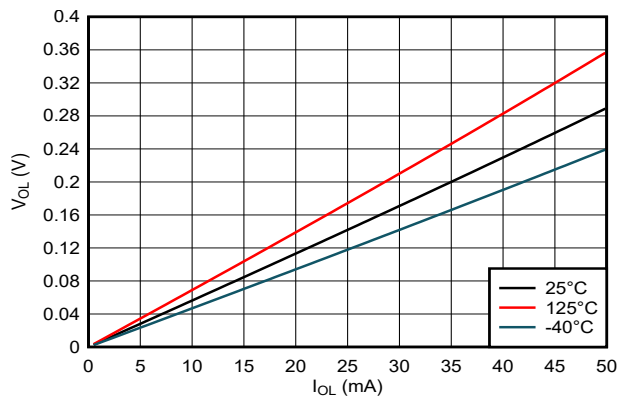
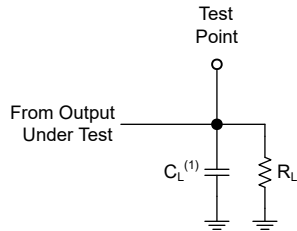


Figure 5-3. Output Voltage vs Current in LOW State; 5V Supply

6 Parameter Measurement Information

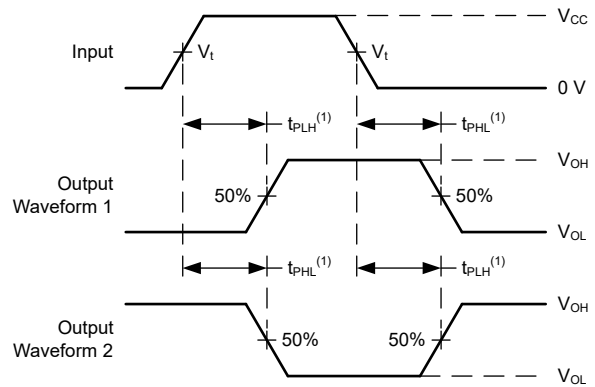
Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{MHz}$, $Z_O = 50\Omega$, $t_t < 2.5\text{ns}$, $V_t = 1.5\text{V}$. For push-pull outputs, $R_L = 500\Omega$.

The outputs are measured individually with one input transition per measurement.



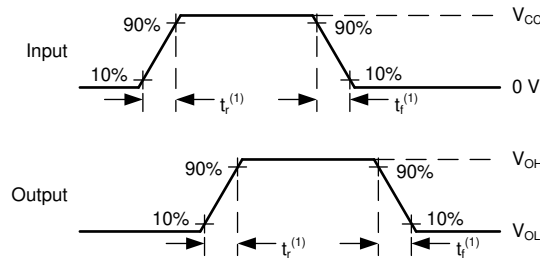
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

Figure 6-3. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

The SN74ACT139-Q1 is a high speed silicon gate CMOS decoder well suited to memory address decoding or data routing applications. It contains two 2:4 decoders.

Each channel of the SN74ACT139-Q1 has two address select inputs (A and B). The circuit functions as a normal one-of-four decoder.

One strobe input (\overline{G}) is provided for each channel to simplify cascading and to facilitate demultiplexing. When the input strobe for a channel is inactive, that channel's outputs are forced into the high state.

The demultiplexing function is accomplished by first using the select inputs to choose the desired output, and then using the strobe input as the data input. The data will appear non-inverted at the selected output.

The outputs for the SN74ACT139-Q1 are normally high, and low when selected.

7.2 Functional Block Diagram

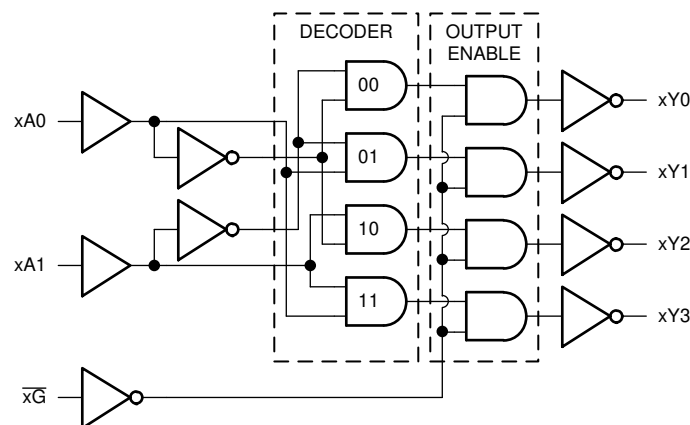


Figure 7-1. Logic Diagram (Positive Logic) for SN74ACT139-Q1 -Q1

7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this

specification will result in excessive power consumption and could cause oscillations. More details can be found in the [Implications of Slow or Floating CMOS Inputs](#) application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10k Ω resistor is recommended and typically will meet all requirements.

7.3.3 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet where packages include this feature.

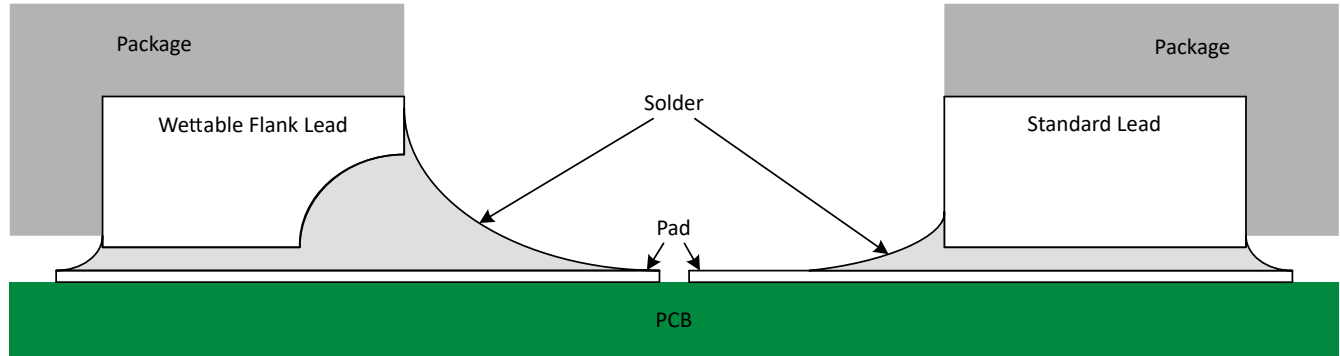


Figure 7-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in [Figure 7-2](#), a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

7.3.4 Clamp Diode Structure

As shown in [Figure 7-3](#), the inputs and outputs to this device have both positive and negative clamping diodes.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

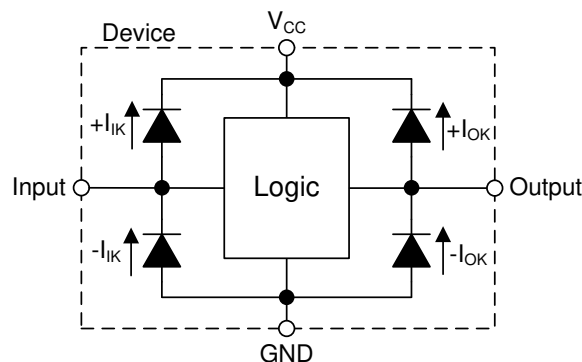


Figure 7-3. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Function Table lists the functional modes of the SN74ACT139-Q1.

Table 7-1. Function Table

INPUTS ⁽¹⁾			OUTPUTS			
n \bar{G}	nA1	nA0	nY0	nY1	nY2	nY3
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L
H	X	X	H	H	H	H

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74ACT139-Q1 device is used to control multiple devices that operate on a shared data bus. A decoder allows a binary encoded input to activate only one of the device's outputs. This makes this device an excellent choice for solid state memory applications where multiple devices have to be read or written to with a limited number of GPIO pins used on the system controller. The decoder is used to activate the chip select (CS) input to the selected memory device, and the controller can then read or write from that device alone when using a shared bus.

8.2 Typical Application

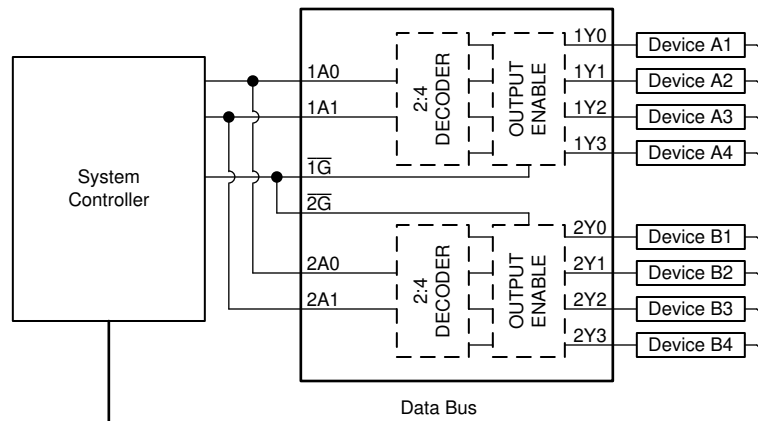


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74ACT139-Q1 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74ACT139-Q1 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74ACT139-Q1 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74ACT139-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74ACT139-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10k Ω resistor value is often used due to these factors.

The SN74ACT139-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is $\leq 50\text{pF}$. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74ACT139-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(\text{max})})\Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in $\text{M}\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

8.2.3 Application Curve

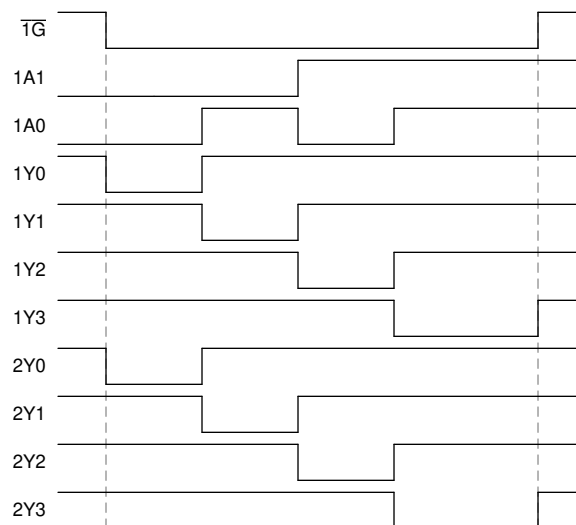


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For the SN74ACT139-Q1, a $0.1\mu\text{F}$ bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of $0.1\mu\text{F}$ and $1\mu\text{F}$ are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
 - Place near the positive supply terminal of the device
 - Provide an electrically short ground return path
 - Use wide traces to minimize impedance
 - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
 - 8mil to 12mil trace width
 - Lengths less than 12cm to minimize transmission line effects
 - Avoid 90° corners for signal traces
 - Use an unbroken ground plane below signal traces

- Flood fill areas around signal traces with ground
- For traces longer than 12cm
 - Use impedance controlled traces
 - Source-terminate using a series damping resistor near the output
 - Avoid branches; buffer signals that must branch separately

8.4.2 Layout Example

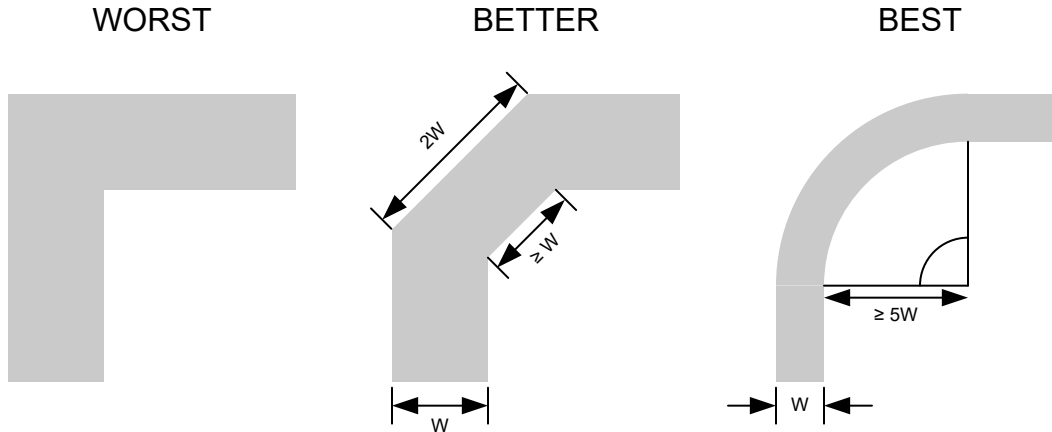


Figure 8-3. Example Trace Corners for Improved Signal Integrity

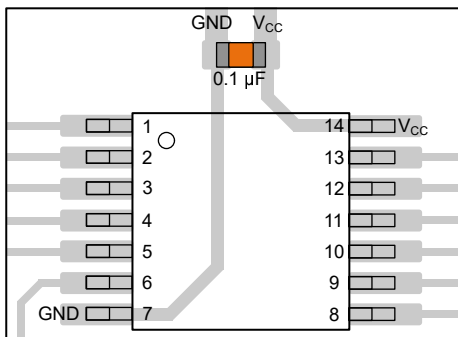


Figure 8-4. Example Bypass Capacitor Placement for TSSOP and Similar Packages

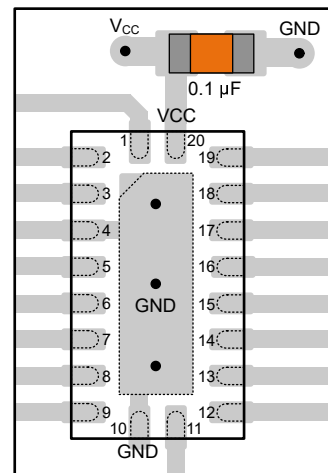


Figure 8-5. Example Bypass Capacitor Placement for WQFN and Similar Packages

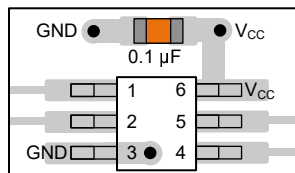


Figure 8-6. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

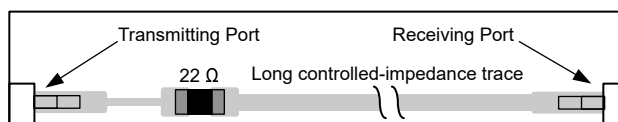


Figure 8-7. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation application report](#)
- Texas Instruments, [Designing With Logic application report](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application report](#)

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
November 2024	*	Initial release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74ACT139PWRQ1	ACTIVE	TSSOP	PW	16		RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ACT139Q	Samples
SN74ACT139WBQBRQ1	ACTIVE	WQFN	BQB	16		RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AD139Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74ACT139-Q1 :

- Catalog : [SN74ACT139](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ACT139PWRQ1	TSSOP	PW	16	0	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74ACT139WBQBRQ1	WQFN	BQB	16	0	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ACT139PWRQ1	TSSOP	PW	16	0	353.0	353.0	32.0
SN74ACT139WBQBRQ1	WQFN	BQB	16	0	210.0	185.0	35.0



4220204/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

BQB 16

WQFN - 0.8 mm max height

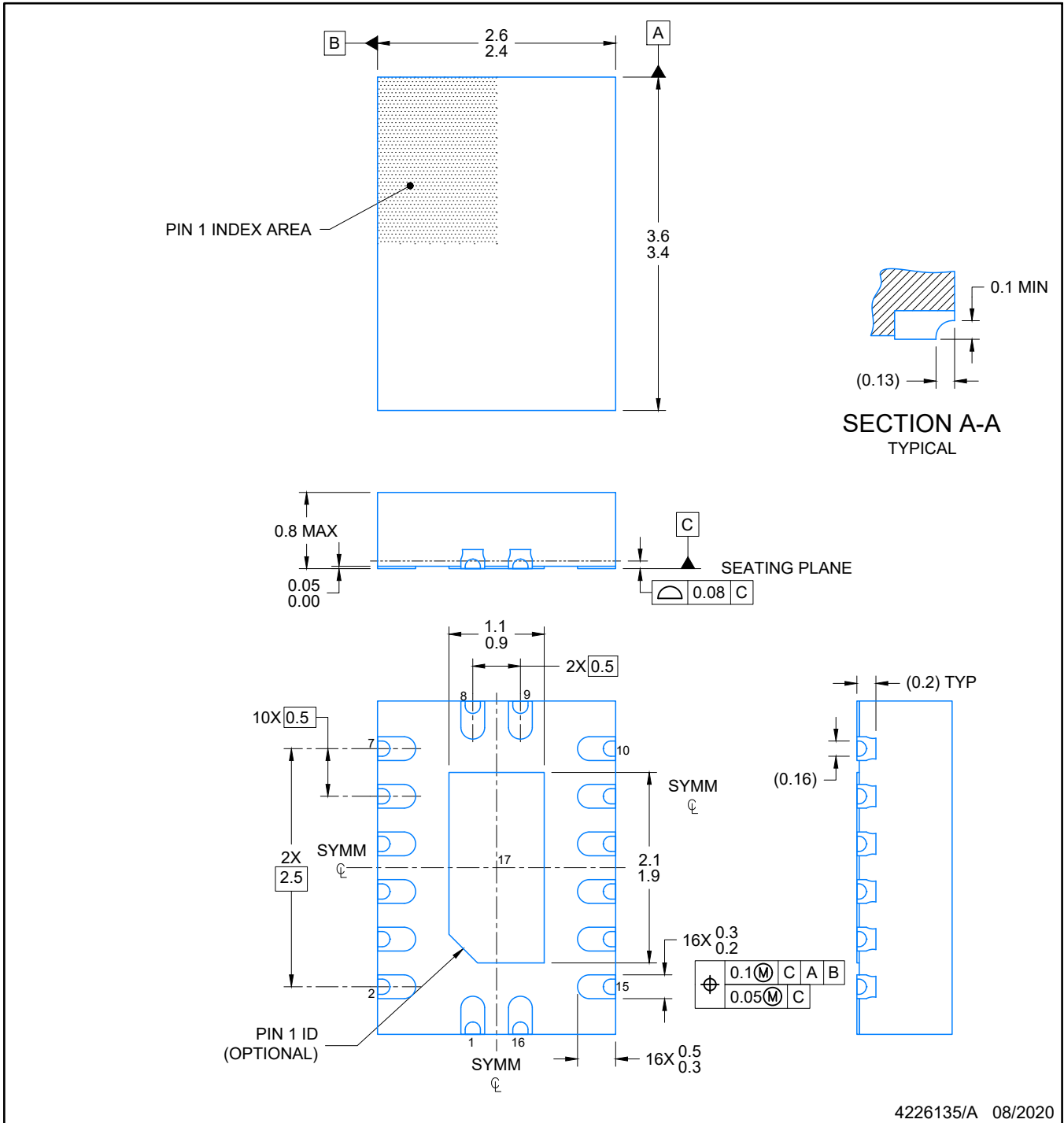
2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4226161/A



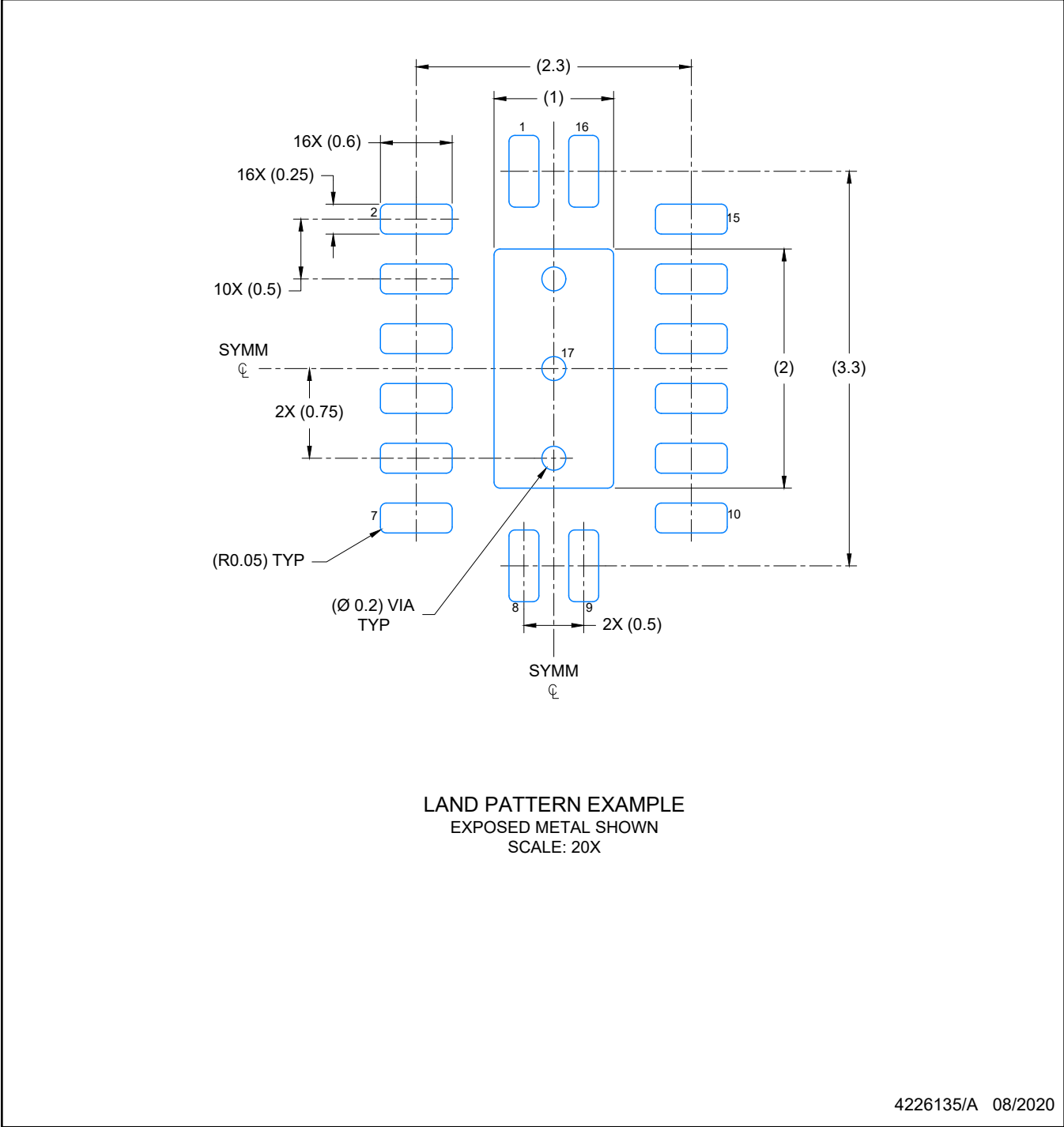
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT
WQFN - 0.8 mm max height

BQB0016B

INDSTNAME



4226135/A 08/2020

NOTES: (continued)

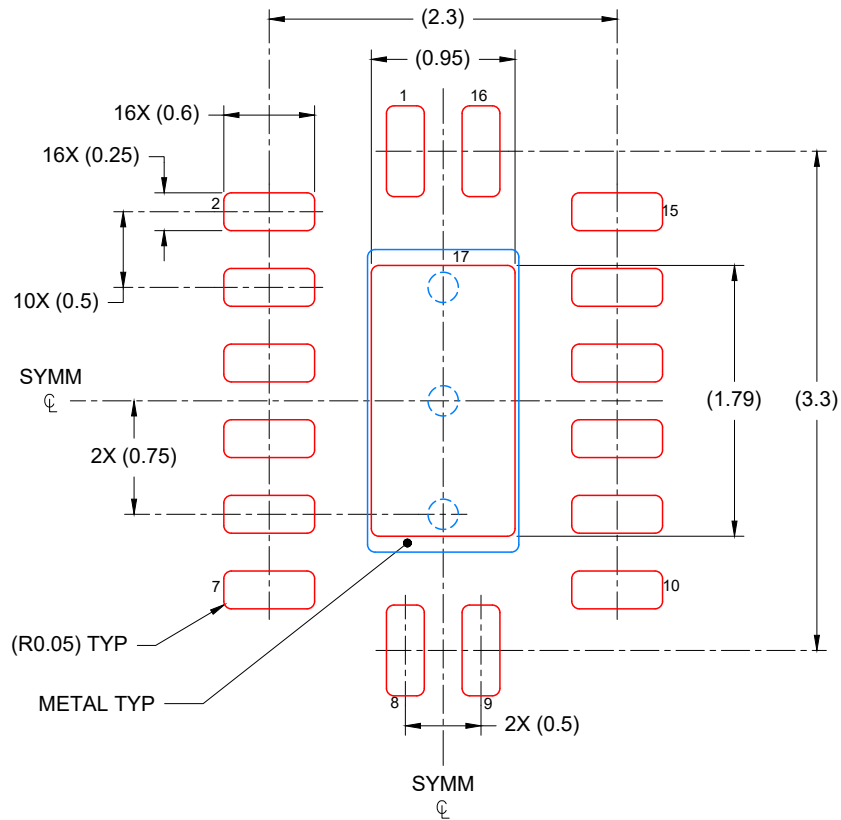
- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

WQFN - 0.8 mm max height

BQB0016B

INDSTNAME



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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